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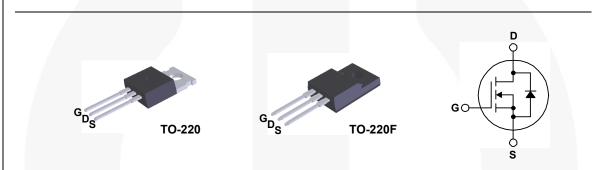
FQP4N90C / FQPF4N90C **N-Channel QFET® MOSFET** 900 V, 4.0 A, 4.2 Ω

Description

This N-Channel enhancement mode power MOSFET is • 4.0 A, 900 V, R_{DS(on)} = 4.2 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 17 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 5.6 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_{D} = 2.0 \text{ A}$



Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter		FQP4N90C	FQPF4N90C	Unit
V _{DSS}	Drain-Source Voltage		9	00	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		4	4 *	А
	- Continuous (T _C = 100°C)	_	2.3	2.3 *	А
ЪМ	Drain Current - Pulsed	(Note 1)	16	16 *	А
V _{GSS}	Gate-Source Voltage		±	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	570		mJ
I _{AR}	Avalanche Current	(Note 1)	4		Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	14		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
PD	Power Dissipation ($T_C = 25^{\circ}C$)		140	47	W
	- Derate above 25°C		1.12	0.38	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		3	°C	

* Drain current limited by maximum junction temperature.

Thermal Characteristics

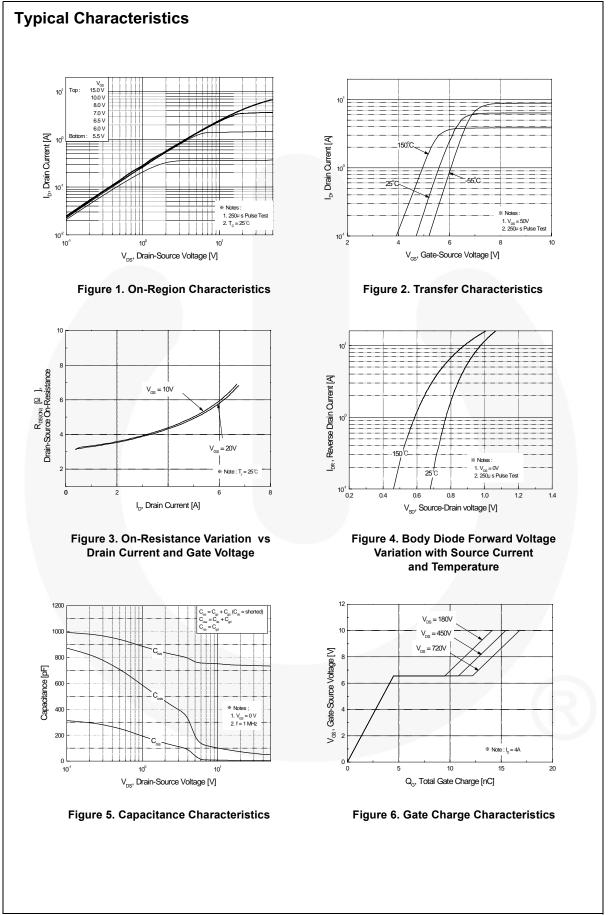
Symbol	Parameter	FQP9N90C	FQPF9N90CT	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.89	2.66	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W	

December 2013

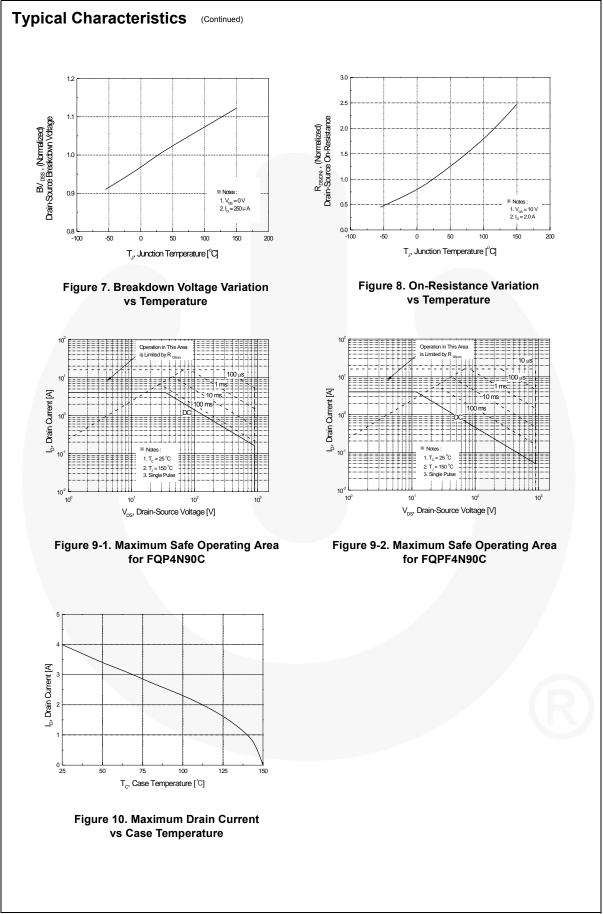
Part NumberTop MarkFQP4N90CFQP4N90C		Pack	ckage Packing Method Reel S		Size	Tape Width		Quantity		
		FQP4N90C	TO-	220	Tube	N/.	A	N/A		50 units
FQPF4N90C FQPF4N90C TO-		TO-2	220F	Tube	N/	Ά	N/A		50 units	
Electric	cal Cha	racteristics	T _C = 25°0	C unless ot	herwise noted.					
Symbol		Parameter			Test Conditions		Min.	Тур.	Max.	Unit
Off Cha	racterist	ics								
BV _{DSS}	Drain-Sou	rce Breakdown Volta	ige	V _{GS} =	0 V, I _D = 250 μA		900			V
ΔBV_{DSS} / ΔT_{J}	Breakdow Coefficient	n Voltage Temperatu t	ire	$I_D = 250 \ \mu$ A, Referenced to 25°C			1.05		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current		$V_{DS} = 900 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$				10	μA		
			V _{DS} = 720 V, T _C = 125°C					100	μA	
I _{GSSF}	Gate-Body	/ Leakage Current, F	orward	$V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$					100	nA
I _{GSSR}	Gate-Body	dy Leakage Current, Reverse		$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA	
On Cha	racterist	ics								
V _{GS(th)}	Gate Thre	shold Voltage		$V_{DS} =$	V_{GS} , $I_D = 250 \ \mu A$		3.0		5.0	V
R _{DS(on)}		ic Drain-Source Resistance		V _{GS} = 10 V, I _D = 2 A			3.5	4.2	Ω	
9 _{FS}	Forward T	Transconductance		$V_{DS} = 50 \text{ V}, I_{D} = 2 \text{ A}$			5		S	
Dynami	ic Charac	teristics								
C _{iss}	Input Capa	acitance		$V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$			740	960	pF	
C _{oss}	Output Ca	t Capacitance		f = 1.0 MHz			65	85	pF	
C _{rss}	Reverse T	ransfer Capacitance					5.6	7.3	pF	
Switchi	ng Chara	acteristics								
t _{d(on)}	Turn-On D		_		450.1/1 4.4			25	60	ns
t _r	Turn-On R		-	$V_{DD} = 450 \text{ V}, \text{ I}_D = 4 \text{ A},$ $R_G = 25 \Omega$				50	110	ns
t _{d(off)}	Turn-Off D	elay Time		$r_G = 2$	20.82			40	90	ns
t _f	Turn-Off F	all Time				(Note 4)		35	80	ns
Qg	Total Gate	Charge		Vne =	720 V, I _D = 4 A,			17	22	nC
Q _{gs}	Gate-Sour	ce Charge		$V_{\rm GS} = 10$ V (Note 4)		/	4.5		nC	
Q _{gd}	Gate-Drain	n Charge					7.5		nC	
	I		stice c	ad Mar	vimum Potinco					
I _S	1	ode Characteris Continuous Drain-S							4	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F								16	Α
V _{SD}		rce Diode Forward V		$V_{GS} = 0 V, I_{S} = 4 A$					1.4	V
t _{rr}		ecovery Time	5		0 V, I _S = 4 A,			450		ns
Q _{rr}		ecovery Charge		$dl_{\rm F}/dt = 100 \text{ A/}\mu\text{s}$				3.5		μC

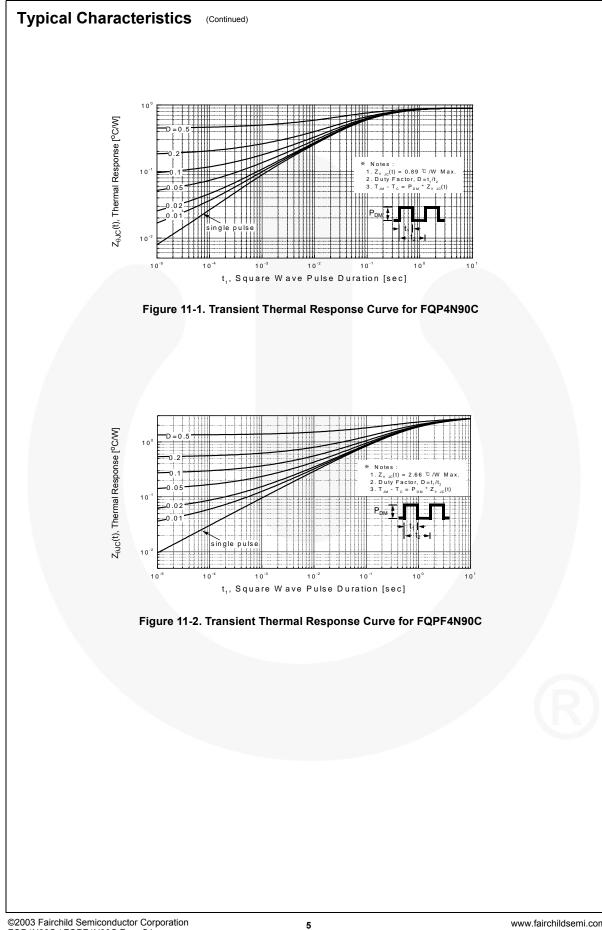
Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 67 mH, I_{AS} = 4 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} ≤ 4 A, di/dt ≤ 200 A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature.

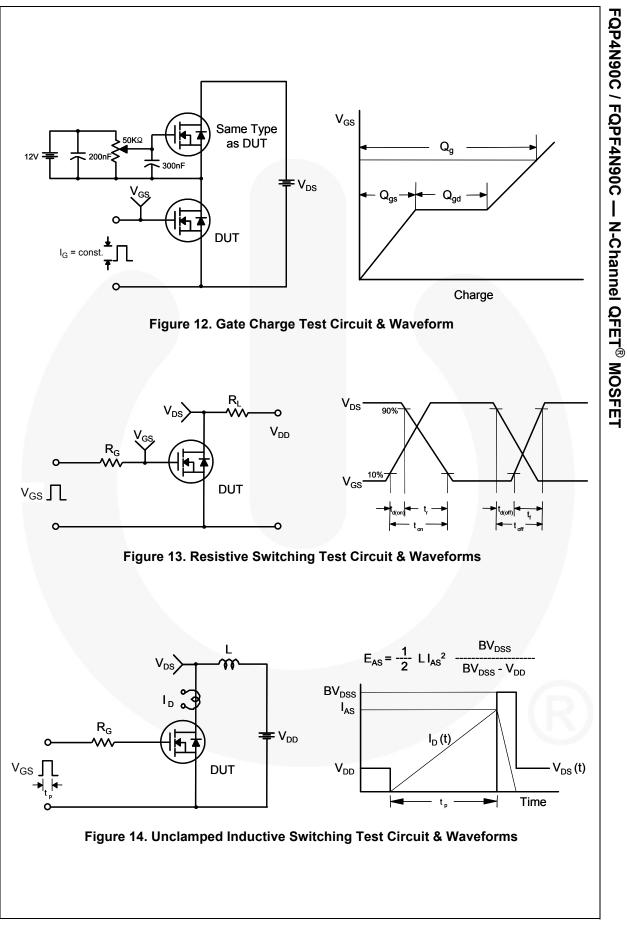
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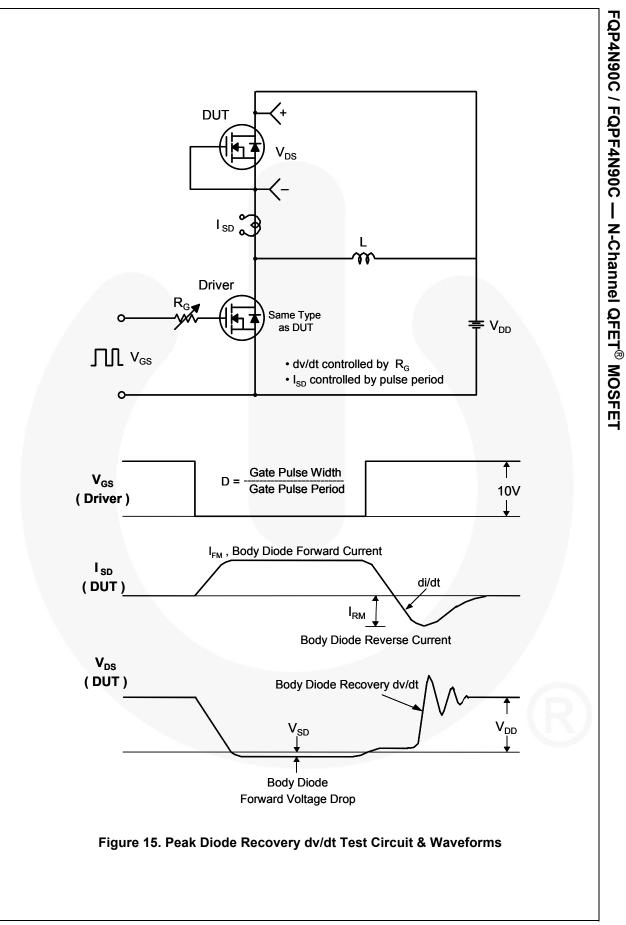


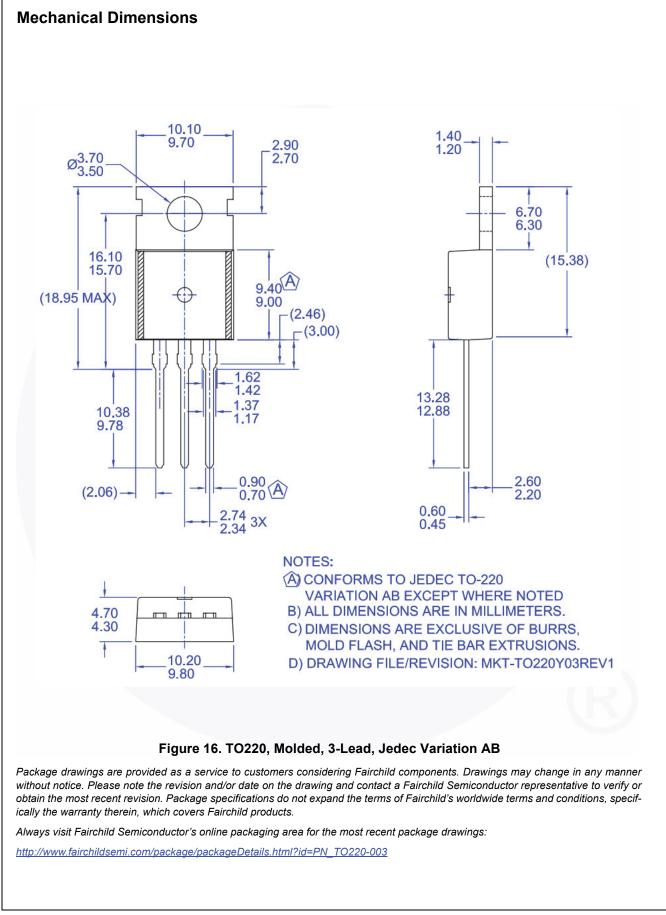
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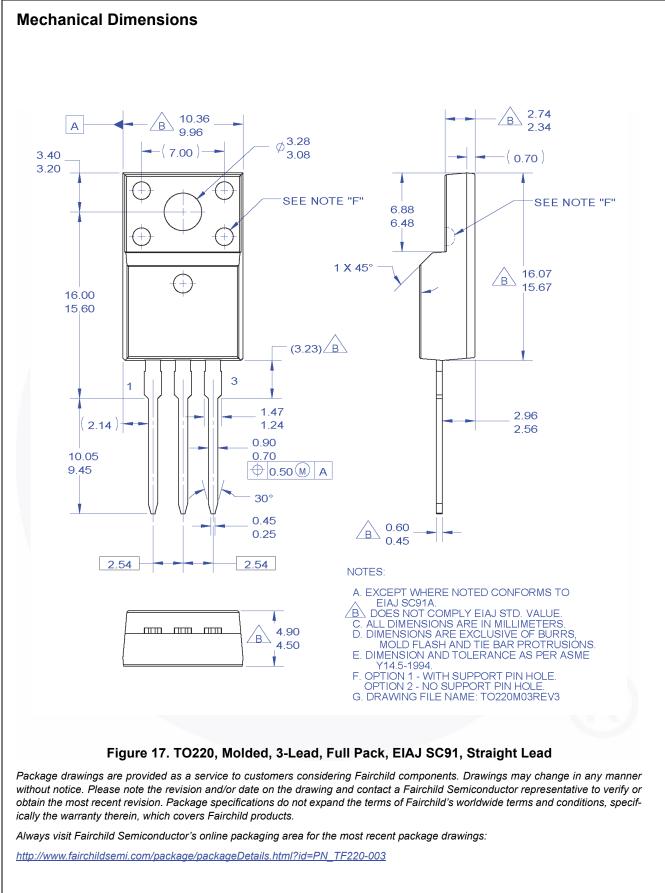












FQP4N90C / FQPF4N90C

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